3.3 V USB 3.1 Single Channel Re-driver

Description

The NB7NPQ701M is a 3.3 V single channel re-driver for USB 3.1 Gen 1 and USB 3.1 Gen 2 applications that supports both 5 Gbps and 10 Gbps data rates. Signal integrity degrades from PCB traces, transmission cables, and inter-symbol interference (ISI). The NB7NPQ701M compensates for these losses by engaging varying levels of equalization at the input receiver and de-emphasis on output driver. The output transmitter circuitry provides user selectable de-emphasis and output amplitude settings to create the best eye openings for the outgoing data signals.

The NB7NPQ701M features an intelligent LFPS circuit. This circuit senses the low frequency signals and automatically disables driver de–emphasis for full USB 3.1 Gen 1 and USB 3.1 Gen 2 compliances.

After power up, the NB7NPQ701M periodically checks both of the TX output pairs for a receiver connection. When the receiver is detected the RX termination becomes enabled and the NB7NPQ701M is set to perform the re-driver function.

The NB7NPQ701M comes in a small, $2 \ge 2 \mod \text{WDFN8}$ package and is specified to operate across the entire industrial temperature range, -40° C to 85° C.

Features

- 3.3 V \pm 5% Power Supply
- Device Supports USB 3.1 Gen 1 and USB 3.1 Gen 2 Data Rates
- Automatic LFPS De-Emphasis Control
- Automatic Receiver Termination Detection
- Integrated Input and Output Termination
- Selectable Equalization, De-Emphasis, and Output Swing
- Hot-Plug Capable
- ESD Protection ±4 kV HBM
- Operating Temperature Range: -40°C to 85°C
- Small 2 x 2 x 0.8 mm WDFN8 Package
- This is a Pb–Free Device

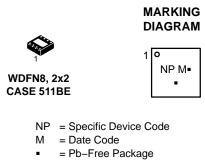
Typical Applications

- Computer and Laptop
- Docking Station and Dongle
- Active Cable, Back Planes
- Gaming Console, Smart T.V.
- Servers and Storage



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(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-----------------|--------------------|-----------------------|
| NB7NPQ701MMTTBG | WDFN8 (Pb–Free) | 3000 / Tape & Reel |

⁺For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

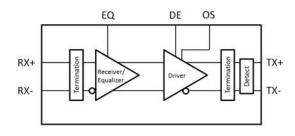


Figure 1. Logic Diagram of NB7NPQ701M

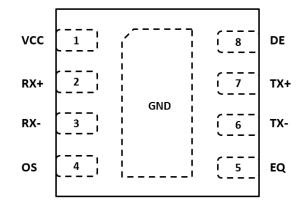


Figure 2. WDFN8 Package Pinout (Top View)

Table 1. PIN DESCRIPTION

| Pin Number | Pin Name | Туре | Description |
|---------------|-------------|-----------|--|
| 1 | VCC | Power | 3.3 V power supply |
| 2 | RX+ | DIFF IN | Differential input pair for 5 / 10 Gbps USB signals. Must be externally AC-coupled. |
| 3 | RX- | | |
| 4 | OS | LVCMOS IN | Sets output swing on the TX. The 3–state input with integrated 250 k Ω pull–up and pull–down resistors. |
| 5 | EQ | LVCMOS IN | Sets the receiver equalizer gain. The 3–state input with integrated 250 k Ω pull–up and pull–down resistors. |
| 6 | TX- | DIFF OUT | Differential output for 5 / 10 Gbps USB signals. Must be externally AC-coupled. |
| 7 | TX+ | | |
| 8 | DE | LVCMOS IN | Sets the output de–emphasis gain. The 3–state input with integrated 250 k Ω pull–up and pull–down resistors. |
| EP | GND | GND | Exposed Pad (EP) on the package bottom is thermally and electronically connected to the die. The exposed pad must electrically connected to GND. |

DEVICE CONFIGURATION

Table 2. CONTROL PIN EFFECTS (Typical Values)

| Pin | Description | Logic State | E | Equalization Gain | | | |
|-----|------------------------------|-------------|----------------------------|-----------------------|-----------|--|--|
| EQ | Equalization Amount | Low | | 3 dB | | | |
| | | Mid | | 6 dB | | | |
| | | High | | 9 dB | | | |
| | | | De-emphasis Ratio (Note 1) | | | | |
| Pin | Description | Logic State | OS = LOW | OS = Float | OS = High | | |
| DE | De-Emphasis Amount | Low | 0 dB | –4.5 dB | –6.5 dB | | |
| | | Mid | -4 dB | –6 dB | –7.5 dB | | |
| | | High | -6 dB | –7.5 dB | –8 dB | | |
| Pin | Description | Logic State | | Output Swing | | | |
| OS | Output Swing with DE Pin Low | Low | | 850 mV _{PP} | | | |
| | (0 dB) | Mid | 1050 mV _{PP} | | | | |
| | | High | | 1200 mV _{PP} | | | |

1. dB Decrease = 20 log * (VTX-DE / VTX-DIFF-PP)

Table 3. ATTRIBUTES

| Parameter | | |
|---|--|----------------------|
| ESD Protection | Human Body Model Charged Device Model | > 4 kV > 1.5 kV |
| Moisture Sensitivity, Indefinite Time Out of Drypack (Note 2) | | Level 1 |
| Flammability Rating | Oxygen Index: 28 to 34 | UL 94 V-O @ 0.125 in |
| Transistor Count | | 703 |
| Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test | | |

2. For additional information, see Application Note AND8003/D.

Table 4. ABSOLUTE MAXIMUM RATINGS

Over operating free-air temperature range (unless otherwise noted)

| Parameter | Description | Min | Max | Unit |
|--|------------------|------|-----------------------|------|
| Supply Voltage (Note 3) | V _{CC} | -0.5 | 4.6 | V |
| Voltage range at any input or | Differential I/O | -0.5 | 1.89 | V |
| output terminal | LVCMOS inputs | -0.5 | V _{CC} + 0.5 | V |
| Storage Temperature Range, T _{SG} | | -65 | 150 | °C |
| Maximum Junction Temperature, T _J | | | 125 | °C |
| Operating Ambient Temperature Range, T _A | | -40 | 85 | °C |
| Junction–to–Ambient Thermal Resistance @ 500 lfm, θ_{JA} (Note 4) | | | 62 | °C/W |
| Wave Solder, Pb–Free, T _{SOL} | | | 265 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

3. All voltage values are with respect to the GND terminals.

4. JEDEC standard multilayer board – 2S2P (2 signal, 2 power).

Table 5. RECOMMENDED OPERATING CONDITIONS

Over operating free-air temperature range (unless otherwise noted)

| Parameter | Description | Min | Nom | Max | Unit |
|-----------------|--------------------------------|-------|-----|-------|------|
| V _{CC} | Main power supply | 3.135 | 3.3 | 3.465 | V |
| T _A | Operating free–air temperature | -40 | | +85 | °C |
| C _{AC} | AC coupling capacitor | 75 | 100 | 265 | nF |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Table 6. POWER SUPPLY CHARACTERISTICS

| | Parameter | Test Conditions | Min | Typ (Note 5) | Max | Unit |
|-----------------|-------------------|--|-----|-----------------|-----|------|
| | Active | Link in U0 with SS data transmission DE = low 0 dB, EQ = low 3 dB, OS = low | | 70 | | mA |
| I _{CC} | Idle State | Link has some activity, not in U0 DE = mid -4 dB, EQ = mid 6dB OS = low | | 50 | | mA |
| | U2/U3 | Link in U2 or U3 power saving state DE = mid –4 dB, EQ = mid 6 dB, OS = low | | 6.7 | | mA |
| | No USB Connection | No connection state, termination disabled DE = mid -4 dB, EQ = mid 6 dB, OS = low | | 6.7 | | mA |

5. TYP values use V_{CC} = 3.3 V, T_{A} = 25°C.

Table 7. LVCMOS CONTROL PIN CHARACTERISTICS

| Parameter | | Test Conditions | Min | Тур | Max | Unit | | | |
|-----------------|------------------------------------|----------------------------------|-----------------------|---------------------|-----------------------|------|--|--|--|
| 3–State LVCMO | 3-State LVCMOS Inputs (EQ, DE, OS) | | | | | | | | |
| V _{IH} | High-level input voltage | | 0.8 * V _{CC} | | V _{CC} | V | | | |
| V _{IM} | Mid-level input voltage | | 0.4 * V _{CC} | V _{CC} / 2 | 0.6 * V _{CC} | V | | | |
| V _{IL} | Low-level input voltage | | GND | | 0.2 * ^V CC | V | | | |
| V _F | Floating voltage | V _{IN} = High impedance | | V _{CC} / 2 | | V | | | |
| R _{PU} | Internal pull-up resistance | | | 250 | | kΩ | | | |
| R _{PD} | Internal pull-down resistance | | | 250 | | kΩ | | | |
| Ι _{ΙΗ} | High-level input current | V _{IN} = 1.89 V | | | 20 | μΑ | | | |
| I _{IL} | Low-level input current | $V_{IN} = GND, V_{CC} = 3.3 V$ | -20 | | | μΑ | | | |

| | Parameter | Test Conditions | Min | Тур | Max | Unit |
|--------------|---|--|-----|---------------------------|------|------------------|
| VRX-DIFF-pp | Input differential voltage swing | AC-coupled, peak-to-peak | 250 | | 1200 | mV _{PP} |
| VRX-CM | Common-mode voltage bias in the receiver (DC) | | | V _{CC} - 0.25 | | V |
| ZRX-DIFF | Differential input impedance (DC) | Present after an USB device is detected on TX+/TX- | 80 | 100 | 120 | Ω |
| ZRX-CM | Common-mode input impedance (DC) | Present after an USB device is detected on TX+/TX- | 20 | 25 | 30 | Ω |
| ZRX-HIGH-IMP | Common-mode input impedance with termination disabled (DC) | Present when no USB device is detected on TX+ | 25 | 35 | | kΩ |
| VTH-LFPS-pp | Low Frequency Periodic Signaling (LFPS) Detect Threshold | Output voltage is considered squelched below this threshold voltage. | | | 300 | mV _{PP} |

Table 8. RECEIVER AC/DC CHARACTERISTICS Over operating free-air temperature range (unless otherwise noted)

Table 9. TRANSMITTER AC/DC CHARACTERISTICS Over operating free-air temperature range (unless otherwise noted)

| | Parameter | Test Conditions | Min | Тур | Max | Unit |
|---|---|---|-----|----------------------|-----------------|------------------|
| VTX-DIFF-PP | Output differential voltage swing at 5 | OS = Low, 50 Ω to V _{CC} | | 850 | | mV _{PP} |
| | Gbps, 10 Gbps with DE low | OS = Mid, 50 Ω to V _{CC} | | 1050 | | |
| | | OS = High, 50 Ω to V _{CC} | | 1200 | | |
| СТХ | TX input capacitance to GND | At 2.5 GHz | | 1.25 | | pF |
| ZTX-DIFF | Differential output impedance (DC) | Present after an USB device is de- tected on TX+/TX- | 80 | 100 | 120 | Ω |
| ZTX-CM | Common-mode output impedance (DC) | Present after an USB device is de- tected on TX+/TX- | 20 | | 30 | Ω |
| ITX-SC | TX short circuit current | TX+ or TX- shorted to GND | | 60 | | mA |
| VTX-CM | Common-mode voltage bias in the transmitter (DC) | | | V _{CC} -0.5 | V _{CC} | V |
| VTX-CM-ACpp | AC common-mode peak-to-peak volt- age swing in active mode | Within U0 and within LFPS | | | 100 | mV _{PP} |
| VTX-IDLE-DIFF- ACpp | Differential voltage swing during electrical idle | Tested with a high–pass filter | 0 | | 10 | mV _{PP} |
| VTX-RXDET | Voltage change to allow receiver detect | Positive voltage to sense receiver termination | | | 600 | mV |
| t _R , t _F | Output rise, fall time | 20% – 80% of differential voltage measured 1 inch from the output pin | | 45 | | ps |
| t _{RF-MM} | Output rise, Fall time mismatch | 20% – 80% of differential voltage measured 1 inch from the output pin | | | 5 | ps |
| t _{diff-LH} , t _{diff-HL} | Differential propagation delay | De-emphasis = -4 dB, OS = Low propagation delay between 50% level at input and output | | 150 | | ps |
| t _{idleEntry} , ^t idleExit | Idle entry and exit times | | | 30 | | ns |

Table 10. TIMING AND JITTER CHARACTERISTICS

| 10 | | ms |
|----|----|----|
| | 10 | 10 |

UI

(Note 8)

UI

(Note 8)

UI

(Note 8)

0.076 Total jitter (Notes 6, 7) TJTX-EYE EQ = Mid 6 dB, DE = High - 6 dB,DJTX Deterministic jitter (Note 7) 0.046 OS = Low 0.004 RJTX Random jitter (Note 7)

JITTER FOR 10 Gbps

| TJTX-EYE | Total jitter (Notes 6, 7) | EQ = Mid 6dB, DE = High −6 dB, OS = Low | 0.053 | UI (Note 8) |
|----------|-------------------------------|--|-------|----------------|
| DJTX | Deterministic jitter (Note 7) | | 0.008 | UI (Note 8) |
| RJTX | Random jitter (Note 7) | | 0.001 | UI (Note 8) |

6. Includes RJ at 10^{-12} .

Measured at the ends of reference channel with a K28.5 pattern, VID = 1000 mVpp, -3.5 dB de-emphasis from source.
 5 Gbps, UI = 200 ps for 10 Gbps, UI = 100 ps.

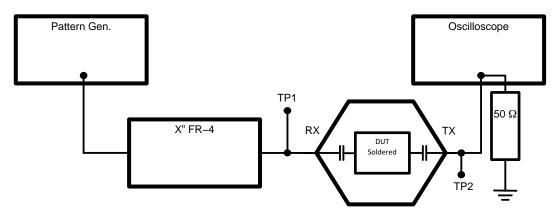


Figure 3. Equalization Measurement Setup

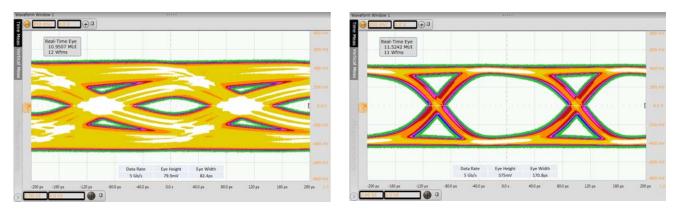


Figure 4. 5 Gbps Signal with 24 inches of FR4 Before Input (Figure 3 TP1) to NB7NPQ701M and After (Figure 3 TP2) Using High EQ Setting

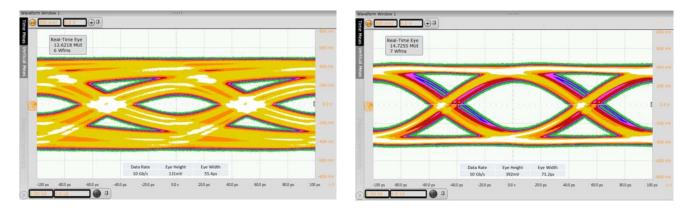
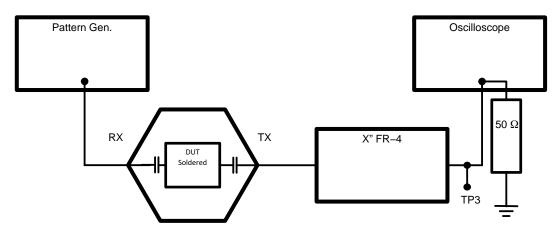
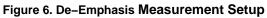


Figure 5. 10 Gbps Signal with 12 inches of FR4 Before Input (Figure 3 TP1) to NB7NPQ701M and After (Figure 3 TP2) with EQ Floating (Mid)





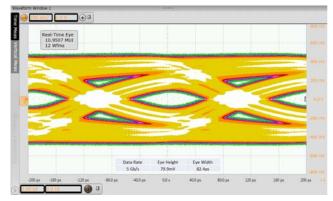


Figure 7. 5 Gbps Signal After 24 inches of FR4 (No DUT)

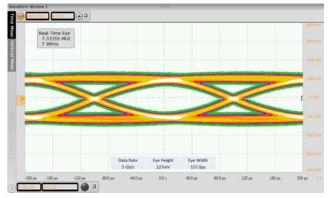


Figure 8. 5 Gbps Signal After 24 inches of FR4 at Output (Figure 6 TP3) with Mid DE Setting to NB7NPQ701M

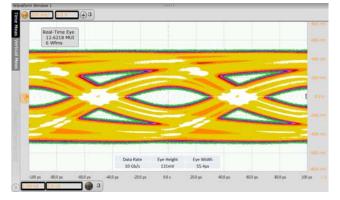


Figure 9. 10 Gbps Signal After 12 inches of FR4 (No DUT)

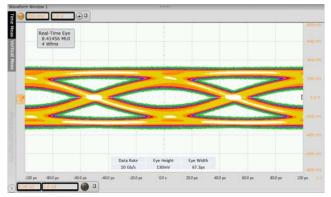


Figure 10. 10 Gbps Signal After 12 inches of FR4 at Output (Figure 6 TP3) with Low DE Setting to NB7NPQ701M

PARAMETER MEASUREMENT DIAGRAMS

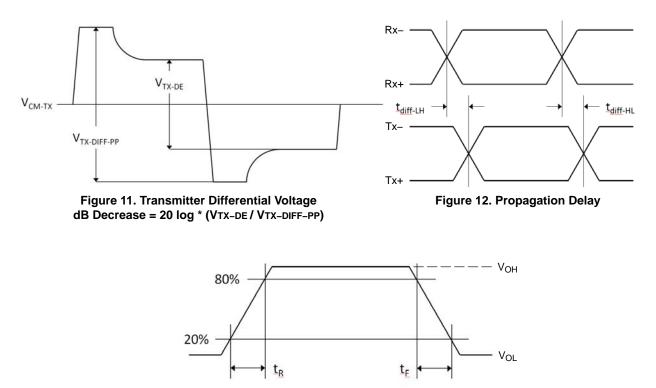


Figure 13. Output Rise and Fall Times

APPLICATION GUIDELINES

LFPS Compliance Testing

As part of USB 3.1 compliance test, the host or peripheral must transmit a LFPS signal that adheres to the spec parameters. When using a real-time oscilloscope to capture this data, *the scope's trigger must be below 0 V when making single-ended measurements*. Although the differential signal is identical to that which is expected by the USB 3.1 system, the AC common mode voltage for LFPS may fall below 0 V during short bursts of switching signal, which is still within the spec's limit.

LFPS Functionality

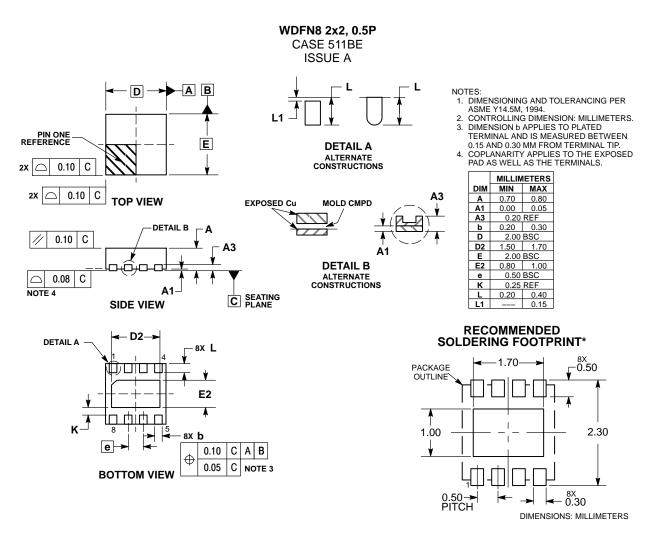
USB 3.1 links use Low Frequency Periodic Signaling (LFPS) to implement functions like exiting low-power modes, performing warm resets and providing link training

between host and peripheral devices. LFPS signaling consists of bursts of frequencies ranging between 10 to 50 MHz and can have specific burst lengths or repeat rates.

Ping.LFPS for TX Compliance

During the transmitter compliance, the system under test must transmit certain compliance patterns as defined by the USB–IF. In order to toggle through these patterns for various tests, the receiver must receive a ping. LFPS signal from either the test suite or a separate pattern generator. The standard signal comprises of a single burst period of 100ns at 20 MHz. In order to pass this signal through NB7NPQ701M, *the duration of the burst must be extended to at least 200 ns.*

PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and solderin details, please download the ON Semiconductor Soldering ar Mounting Techniques Reference Manual, SOLDERRM/D.

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